54ABT573 Octal D-Type Latch with TRI-STATE Outputs

National Semiconductor

54ABT573 Octal D-Type Latch with TRI-STATE[®] Outputs

General Description

The 'ABT573 is an octal latch with buffered common Latch Enable (LE) and buffered common Output Enable $(\overline{\text{OE}})$ inputs.

This device is functionally identical to the 'ABT373 but has different pinouts.

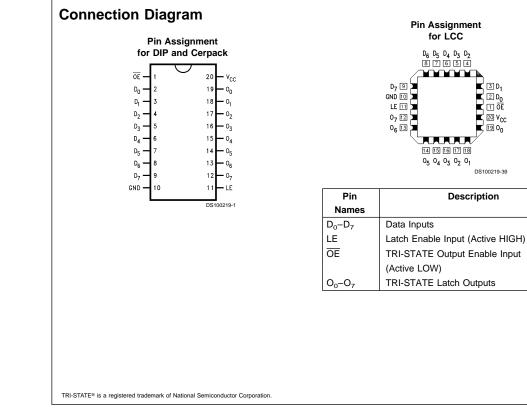
Features

- Inputs and outputs on opposite sides of package allow easy interface with microprocessors
- Useful as input or output port for microprocessors

- Functionally identical to 'ABT373
- TRI-STATE outputs for bus interfacing
- Output sink capability of 48 mA, source capability of 24 mA
- Output switching specified for both 50 pF and 250 pF loads
- Guaranteed latchup protection
- High impedance glitch-free bus loading during entire power up and power down
- Nondestructive hot insertion capability
- Standard Microcircuit Drawing (SMD) 5962-9321901

Ordering Code

| Military | Package Package Description Number | | |
|---------------|------------------------------------|---|--|
| 54ABT573J-QML | J20A | 20-Lead Ceramic Dual-In-Line | |
| 54ABT573W-QML | W20A | 20-Lead Cerpack | |
| 54ABT573E-QML | E20A | 20-Lead Ceramic Leadless Chip Carrier, Type C | |



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Functional Description

The 'ABT573 contains eight D-type latches with TRI-STATE output buffers. When the Latch Enable (LE) input is HIGH, data on the D_n inputs enters the latches. In this condition the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The TRI-STATE buffers are controlled by the Output Enable (\overline{OE}) input. When \overline{OE} is LOW, the buffers are in the bi-state mode. When \overline{OE} is HIGH the buffers are in the high impedance mode but this does not interfere with entering new data into the latches.

Logic Diagram

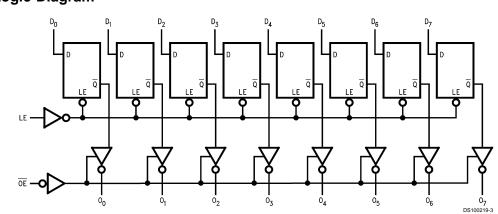
| Function Table | | | | | | | | |
|----------------|---------|---|---------------------|--|--|--|--|--|
| | Outputs | | | | | | | |
| ŌE | LE | D | 0 | | | | | |
| L | н | Н | Н | | | | | |
| L | н | L | L | | | | | |
| L | L | Х | 0 ₀ 7 | | | | | |
| н | х | Х | Z | | | | | |

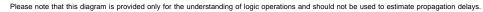
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H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial $O_0 = Value$ stored from previous clock cycle





Absolute Maximum Ratings (Note 1)

| _ | |
|----------------------------------|--------------------------------------|
| Storage Temperature | –65°C to +150°C |
| Ambient Temperature under Bias | –55°C to +125°C |
| Junction Temperature under Bias | |
| Ceramic | –55°C to +175°C |
| V _{CC} Pin Potential to | |
| Ground Pin | -0.5V to +7.0V |
| Input Voltage (Note 2) | -0.5V to +7.0V |
| Input Current (Note 2) | -30 mA to +5.0 mA |
| Voltage Applied to Any Output | |
| in the Disabled or | |
| Power-Off State | -0.5V to +5.5V |
| in the HIGH State | –0.5V to V _{CC} |
| Current Applied to Output | |
| in LOW State (Max) | Twice the rated I _{OL} (mA) |
| DC Latchup Source Current | –500 mA |

Over Voltage Latchup (I/O)

Recommended Operating Conditions

| Free Air Ambient Temperature | |
|---|-------------------------|
| Military | –55°C to +125°C |
| Supply Voltage | |
| Military | +4.5V to +5.5V |
| Minimum Input Edge Rate | $(\Delta V / \Delta t)$ |
| Data Input | 50 mV/ns |
| Enable Input | 20 mV/ns |
| Note 1: Absolute maximum ratings are values be damaged or have its useful life impaired. Fu conditions is not implied. | |

Note 2: Either voltage limit or current limit is sufficient to protect inputs.

DC Electrical Characteristics

| Symbol | Para | Parameter ABT573 Uni | | Units | Vcc | Conditions | | | |
|------------------|-----------------------------------|----------------------|------|-------|------|------------|----------|--|--|
| | | | Min | Тур | Max | 1 | | | |
| VIH | Input HIGH Voltage | | 2.0 | | | V | | Recognized HIGH Signal | |
| V _{IL} | Input LOW Voltage | | | | 0.8 | V | | Recognized LOW Signal | |
| V _{CD} | Input Clamp Diode Volt | age | | | -1.2 | V | Min | I _{IN} = -18 mA | |
| V _{OH} | Output HIGH Voltage | 54ABT | 2.5 | | | V | Min | I _{OH} = -3 mA | |
| | | 54ABT | 2.0 | | | | | I _{OH} = -24 mA | |
| V _{OL} | Output LOW Voltage | 54ABT | | | 0.55 | V | Min | I _{OL} = 48 mA | |
| I _{IH} | Input HIGH Current | | | | 5 | μA | Max | V _{IN} = 2.7V (Note 4) | |
| | | | | | 5 | | | V _{IN} = V _{CC} | |
| I _{BVI} | Input HIGH Current | | | | 7 | μA | Max | V _{IN} = 7.0V | |
| | Breakdown Test | | | | | | | | |
| IIL | Input LOW Current | | | | -5 | μA | Max | V _{IN} = 0.5V (Note 4) | |
| | | | | | -5 | | | $V_{IN} = 0.0V$ | |
| V _{ID} | Input Leakage Test | | 4.75 | | | V | 0.0 | I _{ID} = 1.9 μA | |
| | | | | | | | | All Other Pins Grounded | |
| I _{OZH} | Output Leakage Curren | t | | | 50 | μA | 0 – 5.5V | $V_{OUT} = 2.7V; \overline{OE} = 2.0V$ | |
| I _{OZL} | Output Leakage Curren | t | | | -50 | μA | 0 – 5.5V | $V_{OUT} = 0.5V; \overline{OE} = 2.0V$ | |
| I _{OS} | Output Short-Circuit Cu | rrent | -100 | | -275 | mA | Max | V _{OUT} = 0.0V | |
| I _{CEX} | Output High Leakage C | urrent | | | 50 | μA | Max | V _{OUT} = V _{CC} | |
| I _{ZZ} | Bus Drainage Test | | | | 100 | μA | 0.0 | V _{OUT} = 5.5V; All Others GND | |
| I _{CCH} | Power Supply Current | | | | 50 | μA | Max | All Outputs HIGH | |
| I _{CCL} | Power Supply Current | | | | 30 | mA | Max | All Outputs LOW | |
| I _{CCZ} | Power Supply Current | | | | 50 | μA | Max | OE = V _{CC} | |
| | | | | | | | | All Others at V _{CC} or GND | |
| I _{CCT} | Additional I _{CC} /Input | Outputs Enabled | | | 2.5 | mA | | $V_{I} = V_{CC} - 2.1V$ | |
| | | Outputs TRI-STATE | | | 2.5 | mA | Max | Enable Input V _I = V _{CC} - 2.1V | |
| | | Outputs TRI-STATE | | | 2.5 | mA | | Data Input V _I = V _{CC} - 2.1V | |
| | | | | | | | | All Others at V_{CC} or GND | |
| I _{CCD} | Dynamic I _{CC} | No Load | | | | mA/ | Max | Outputs Open | |
| | (Note 4) | | | | 0.12 | MHz | | \overline{OE} = GND, LE = V _{CC} (Note 3) | |
| | | | | | | | | One Bit Toggling, 50% Duty Cycle | |

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Note 3: For 8 bits toggling, $I_{\rm CCD}$ < 0.8 mA/MHz.

Note 4: Guaranteed but not tested.

10V

| DC | Electrical | Characteristics |
|----|-------------------|-----------------|
| | | Characteristics |

| Symbol | Parameter | Min | Max | Units | V _{cc} | Conditions |
|------------------|--|-----|------|-------|-----------------|---|
| | | | | | | C_{L} = 50 pF, R_{L} = 500 Ω |
| V _{OLP} | Quiet Output Maximum Dynamic V _{OL} | | 0.9 | V | 5.0 | $T_A = 25^{\circ}C$ (Note 5) |
| V _{OLV} | Quiet Output Minimum Dynamic V _{OL} | | -1.7 | V | 5.0 | $T_A = 25^{\circ}C$ (Note 5) |

Note 5: Max number of outputs defined as (n). n – 1 data inputs are driven 0V to 3V. One output at LOW. Guaranteed, but not tested.

AC Electrical Characteristics

| Symbol | Parameter | 54ABT T _A = -55°C to +125°C | | Units | Fig. No. | |
|------------------|----------------------------------|---|------------|-------|-------------|--|
| | Γ | | | | | |
| | | $V_{\rm CC} = 4.5$ | iV to 5.5V | | | |
| | | C _L = | 50 pF | | | |
| | Γ | Min | Max | | | |
| t _{PLH} | Propagation Delay | 1.0 | 6.4 | ns | Figure 4 | |
| t _{PHL} | D _n to O _n | 1.5 | 6.7 | | | |
| t _{PLH} | Propagation Delay | 1.0 | 7.1 | ns | Figure 4 | |
| t _{PHL} | LE to O _n | 1.5 | 7.5 | | | |
| t _{PZH} | Output Enable Time | 0.8 | 6.5 | ns | Figure 6 | |
| t _{PZL} | | 1.5 | 7.2 | | | |
| t _{PHZ} | Output Disable Time | 1.5 | 7.7 | ns | Figure 6 | |
| t _{PLZ} | Time | 1.0 | 7.0 | | | |

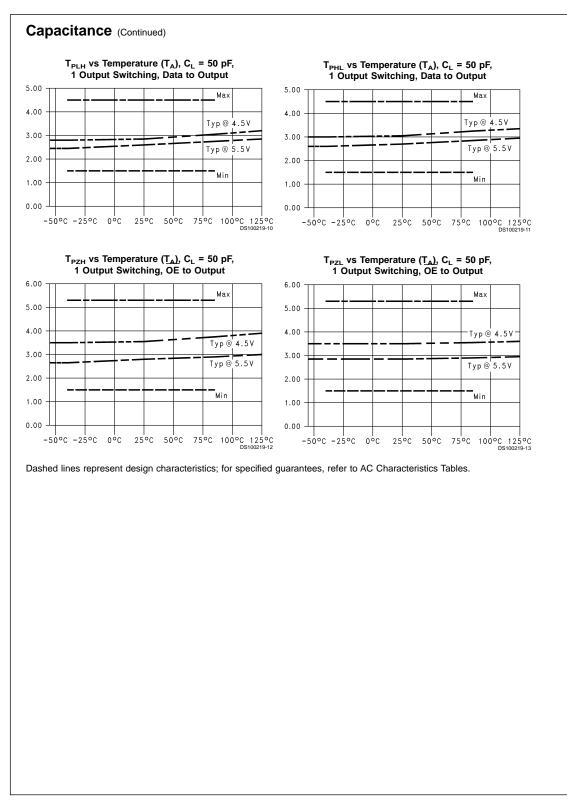
AC Operating Requirements

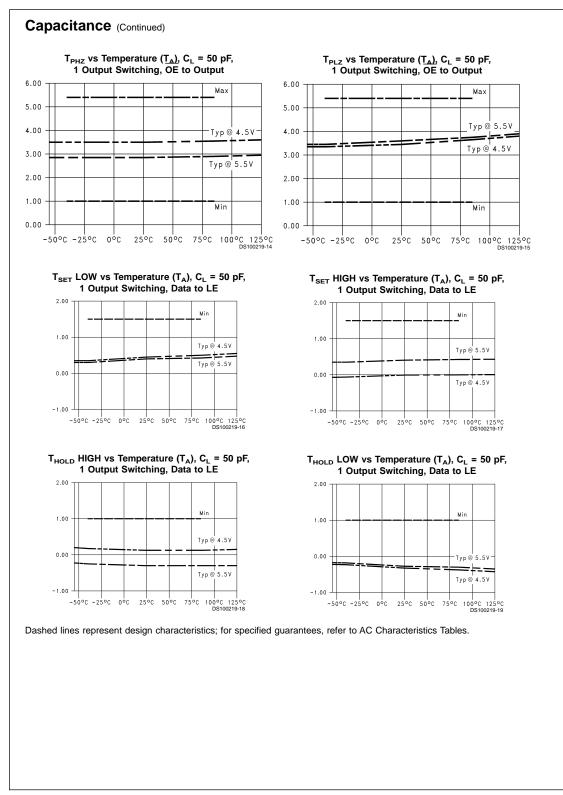
| Symbol | Parameter | $\frac{54ABT}{T_{A} = -55^{\circ}C \text{ to } +125^{\circ}C}$ $V_{CC} = 4.5V \text{ to } 5.5V$ $C_{L} = 50 \text{ pF}$ | | Units | Fig. No. |
|--------------------|-----------------------------|---|-----|-------|-------------|
| | | Min | Max | | |
| t _s (H) | Set Time, HIGH | 2.5 | | ns | Figure 7 |
| t _s (L) | or LOW D _n to LE | 2.5 | | | |
| t _h (H) | Hold Time, HIGH | 2.5 | | ns | Figure 7 |
| t _h (L) | or LOW D _n to LE | 2.5 | | | |
| t _w (H) | Pulse Width, | 3.3 | | ns | Figure 5 |
| | LE HIGH | | | | |

Capacitance

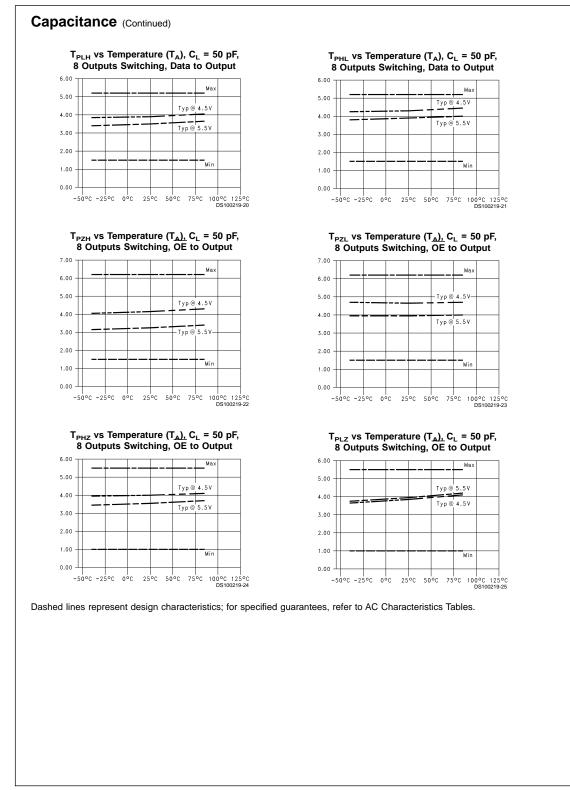
| Symbol | Parameter | Тур | Units | Conditions | | |
|---|--------------------|-----|-------|-------------------------|--|--|
| | | | | (T _A = 25°C) | | |
| C _{IN} | Input Capacitance | 5 | pF | $V_{CC} = 0V$ | | |
| C _{OUT} (Note 6) | Output Capacitance | 9 | pF | $V_{CC} = 5.0V$ | | |
| Note C. C. is measured at fragmany (A Mile and Mile OTD 000D Mathed 0040 | | | | | | |

Note 6: C_{OUT} is measured at frequency f = 1 MHz per MIL-STD-883B, Method 3012.

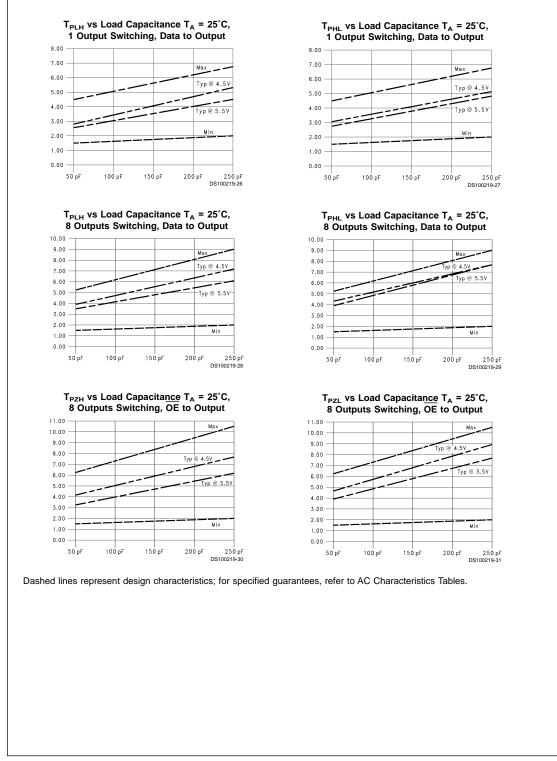


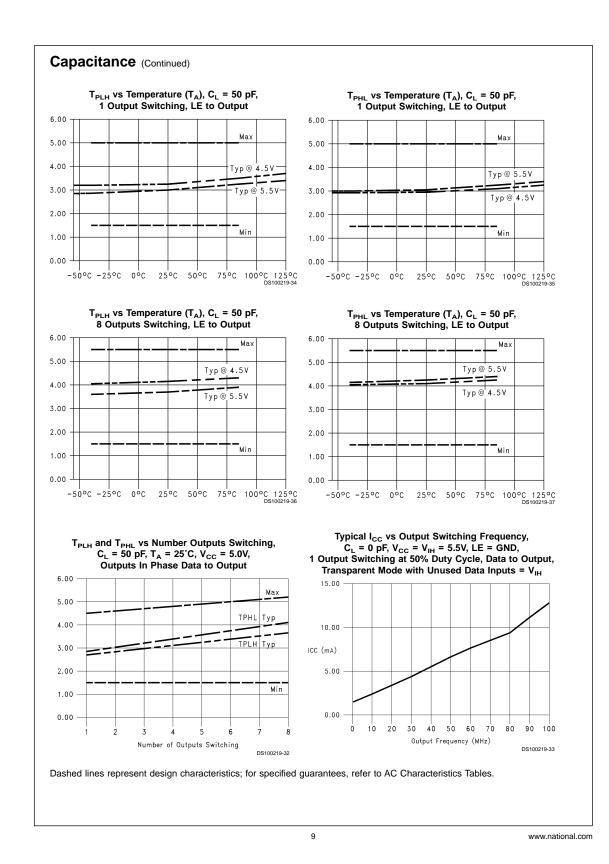


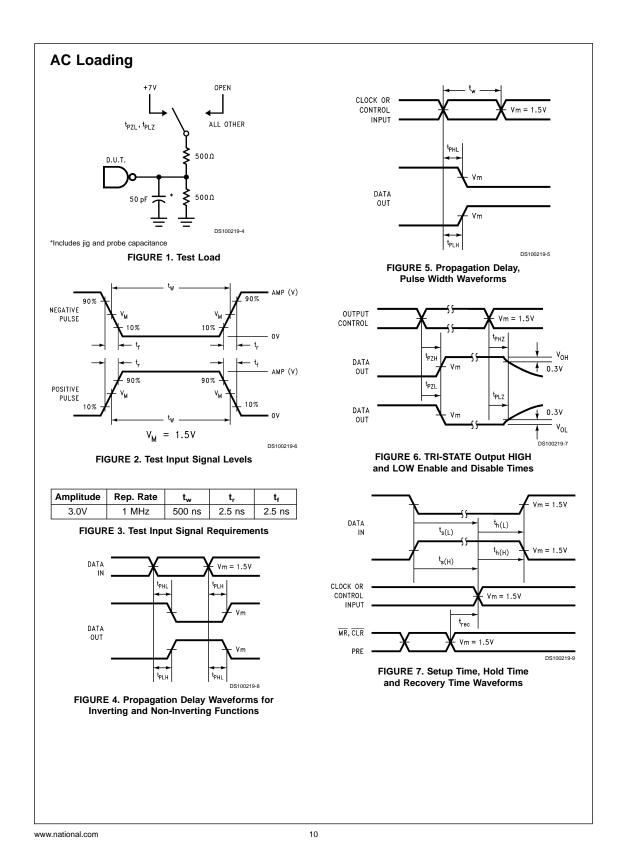
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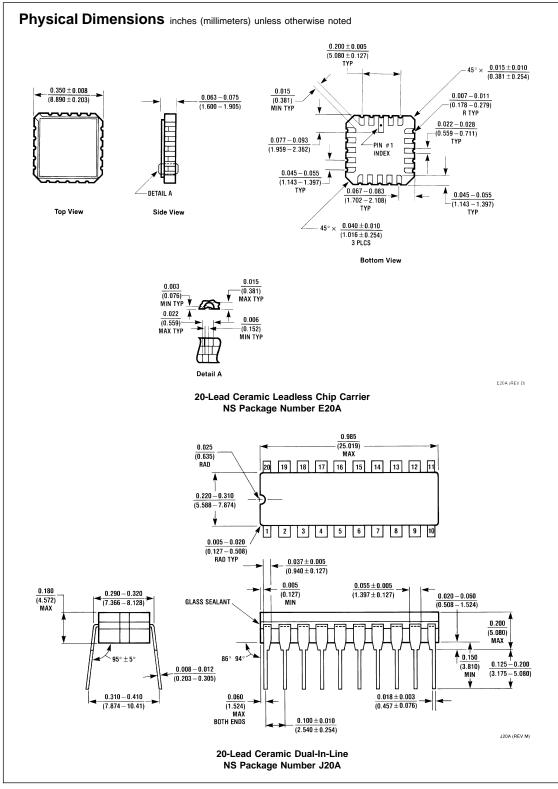


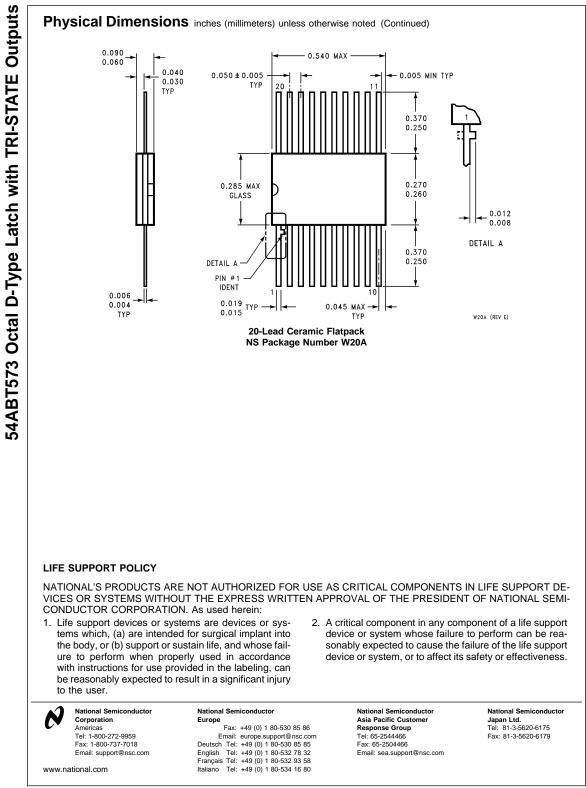






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